

## CLAIM AMENDMENTS

### IN THE CLAIMS

This listing of the claims will replace all prior versions, and listing, of claims in the application or previous response to office action:

1. **(Currently Amended)** A power semiconductor module comprising a plurality of semiconductor components situated on a substrate, wherein
  - the substrate is divided into a plurality of separate substrate regions and
  - one or a plurality of connecting regions are ~~situated~~ arranged in between adjacent substrate regions, wherein said connecting region are designed ~~such to prevent a deformation that a movement~~ of one substrate region[s] ~~does not translate to continue~~ to an adjacent substrate region.
2. **(Previously Presented)** The power semiconductor module as claimed in claim 1, wherein
  - the connecting regions are formed by recesses in a module housing enclosing said substrate regions.
3. **(Original)** The power semiconductor module as claimed in claim 2, wherein
  - the material recesses are slotted.
4. **(Original)** The power semiconductor module as claimed in claim 1, wherein
  - the substrate is a ceramic.
5. **(Original)** The power semiconductor module as claimed in claim 2, wherein
  - the substrate is a ceramic.
6. **(Canceled)**
7. **(Canceled)**

8. (Previously Presented) The power semiconductor module as claimed in claim 2, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

9. (Previously Presented) The power semiconductor module as claimed in claim 3, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

10. (Canceled)

11. (Original) The power semiconductor module as claimed in claim 5, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

12. (Original) The power semiconductor module as claimed in claim 6, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

13. (Original) The power semiconductor module as claimed in claim 1, wherein

- the power semiconductor module has a housing, which, in the region between the substrate regions, has action points for a mechanical pressure application of the connecting regions, and
- the housing applies pressure to the individual substrate regions.

14. (Currently Amended) A power semiconductor module comprising  
- a plurality of substrate elements having top and bottom surface, each substrate element comprising a semiconductor component arranged on the top surface of a substrate element;

- one or a plurality of connecting regions arranged in between adjacent substrate regions to form a continuous bottom surface, wherein said connecting region are designed to prevent a deformation such that a movement of one substrate region[s] does not translate to continue to an adjacent substrate region.

15. (Previously Presented) The power semiconductor module as claimed in claim 14, further comprising a module housing enclosing said plurality of substrate elements.

16. (Previously Presented) The power semiconductor module as claimed in claim 15, wherein

- the connecting regions are formed by recesses in the module housing.

17. (Previously Presented) The power semiconductor module as claimed in claim 16, wherein

- the material recesses are slotted.

18. (Previously Presented) The power semiconductor module as claimed in claim 14, wherein

- the substrate is a ceramic.

19. (Previously Presented) The power semiconductor module as claimed in claim 15, wherein

- the module housing, at least in the regions of the substrate elements, is such that it acts on the substrate elements with a spring force.

20. (Currently Amended) The power semiconductor module as claimed in claim 14, further comprising

- a heat sink having a flat surface, wherein the continuous bottom surface of the plurality of substrate elements and said plurality of connecting regions areis arranged on said flat surface.

21. (Previously Presented) The power semiconductor module as claimed in claim 15, wherein

- the module housing in the region between the substrate elements comprises action points for a mechanical pressure application of the connecting regions, and  
- the housing applies pressure to the individual substrate elements.

22. (NEW) The power semiconductor module as claimed in claim 1, further comprising

- a heat sink having a flat surface, wherein the continuous bottom surface of the plurality of substrate elements and said plurality of connecting regions are arranged on said flat surface.

23. (NEW) A power semiconductor module comprising:

- a heat sink having a flat surface,  
- a plurality of substrates arranged on the flat surface of the heat sink;  
- a plurality of semiconductor components arranged on the substrates,  
- one or a plurality of connecting regions arranged on the flat surface of the heat sink between adjacent substrate regions, wherein the connecting regions are designed to prevent a deformation of one substrate region to continue to an adjacent substrate region.